

RO Chip Power

Low power matters for module thermal management. Low current matters for cable losses. Reducing current is more effective than optimizing cable resistance/rad. length (I^2R) . Reduced currents will greatly simplify power distribution and power electronics.

ATLAS strips ROIC history and future (current per 128-channel chip)

	ABCD 0.8 µm bi-CMOS		ABC-Next 0.25 µm CMOS		ABC-Next 0.13 µm CMOS	
	V [V]	I [mA]	V [V]	I [mA]	V [V]	I [mA]
analog	3.5	~ 80	2.2	~ 36	1.2	~17
digital	4	~ 40	2.5	~ 120	0.9	60-120

Value depends on need for SEU protection

Analog voltage will be higher than digital voltage!

For 0.25 µm ABC-Next analog voltage is derived from digital.

 \Leftrightarrow ~300 mV difference between V_{cc} and V_{dd} is natural.

What for 0.13 µm ABC-Next? Expect digital voltage to be derived from analog.

(Rather than separate power lines or DC-DC step-up or step-down conversion.)

 \Leftrightarrow A voltage difference of more than ~300 mV difference between V_{cc} and V_{dd} does not help

RO Chip Power (continued)

- Digital power will be significantly higher than analog power for short strips
 - ⇔ focus on digital current reduction now
- Constant current consumption vs. lower (average) current

My prejudice is that constant current will be very beneficial for optimum hybrid performance \$\Rightarrow\$ simply switching clocks off where possible might not be enough

What could be done?

I have no obvious answer, but feel that much more than incremental power savings are possible (at cell level; chip level; system level)



Analyze where digital power is spent and identify improvements; optimize RO architecture for power; put common logic into module controller chip; Increase number of channels per chip, etc.

DC-DC critical issues

Disclaimer: I will only mention two, which I feel are most urgent to date

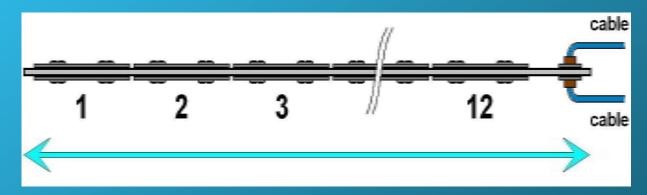
DC-DC converter induced "pick-up"

Excess noise through coupling between air-coil and strips has been observed by several groups (Yale, RAL, BNL, Aachen). The size of the effect depends on shielding, distance to sensor, etc. Our target should be "zero" excess noise. I believe this is achievable.

We will get more results when the first upgrade prototype modules become available. For ATLAS this might happen by the end of this year.

• DC-DC converter gain

So far we have been limited to gain 4. We need to be more ambitious. Either by gain ~10 devices (preferred) or two stage converter systems. The example below shows why



Efficiency examples

Disclaimer: My numbers are just reasonable guesses and contain several simplifications. Put in your own numbers!

Assumptions: hybrid current/voltage/power: 2 A/1.2 V/ 2.4 W;

cable resistance: 2 Ohms ⇔ these numbers are optimistic

20 hybrids per stave side; ⇔ 48 W per stave side; regulator/converter inefficiency: 15%

(for SP the inefficiency considers current variations with time and between modules)

Four scenarios

a	SP with 20 hybrids in series; inefficiency 15%	⇔ ~ 11 W cable losses
$\sim \iota$	DI Will 20 Hydrias in series, inefficiency 1570	TI W Cable tobbeb

<i>b</i>)	DC DC with agin 10, in efficiency 150/	/ AAW logger
\mathcal{O}	DC-DC with gain 10; inefficiency 15%	<i>⇔</i> ~ 44 W losses

c)
$$DC$$
- DC with gain $4 * 2$; inefficiencies 15% and 10% $\Leftrightarrow \sim 85$ W losses

This suggests:

Let's work hard for high gain! We can do better than a gain of four.

DC-DC with gain 10 keeps power efficiency at LHC levels. This is would be a great achievement.

Serial powering with 20 or more hybrids in series is even better

Serial powering critical issues

• Custom SP circuitry

We are almost there. Design of custom circuitry for strips and of the general purpose SPi chip for strips or pixels was a major enterprise. Getting functional chips back will clearly make a huge difference for this R&D.

Need to explore all three architectures and understand which is most suitable for the final system. Only one can be taken. Which one is entirely open as of today.

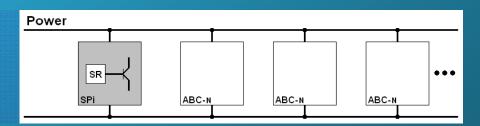
All-internal scheme

Parallel shunt regulators & shunt transistors ATLAS pixels (Bonn) and strips (W. Dabrowski)

Power SR SR SR ABC-N ABC-N ABC-N

All-external scheme/SPi scheme

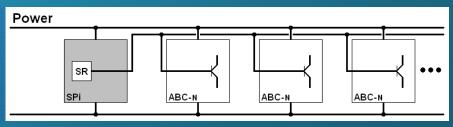
One external shunt regulator and transistor M. Trimpl (FNAL), RAL, UPenn



Mixed scheme

One external shunt regulator – many parallel shunt transistors

M. Newcomer (UPenn)



Serial powering protection schemes

The risk of losing all modules in series through a fault is an obvious concern with serial powering. While the reduced number of connections provides some protection, more can be done.

(Protection is also important for DC-DC in particular with parallel powering, less with independent powering)

There are two distinct tasks

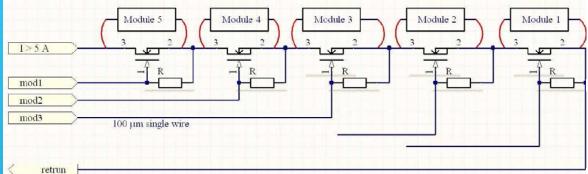
- 1) Slow-control: switch module to stand-by (lowest achievable voltage across it); bridge broken current path.
- 2) Real-time protection: over-voltage; excessive power through shunt transistor

The best schemes is yet to be found, but for the next round of supermodule construction, we should implement the best we can. This will be discrete components.

Conceptual schemes in the making

Bonn scheme

Power FET driven by slow-control shorts module to reduce thermal load or for a fault.

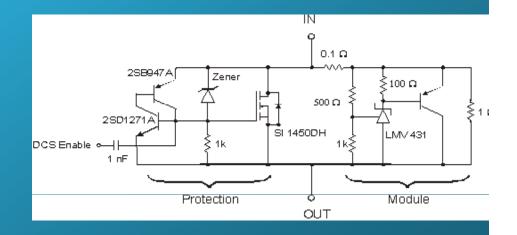


Simple; low-voltage drop; the extra control lines can be used for voltage sensing

BNL scheme

Overvoltage protection, latch and alternative current path.

Real-time protection and stand-by enabled through slow-control; one-wire system



• SPi protection features

Low-voltage mode and current sensing ADC plus current alarm. No real-time activation of protection in this iteration

Serial powering protection (continued)

A little more thinking and simulation is needed to identify the optimum scheme.

Questions to address:

- Where to place the protection circuitry (on or off-hybrid)?
- Individual control lines or one-wire system?
- Optimum schematic (e.g. how to achieve low voltage drop)
- How to combine protection elements in one chip or how minimize the number of technologies

Choices may well be system dependent and be different for strips and pixels.

Need to gain practical experience with these schemes.

ATLAS next steps

Hope to build a prototype silicon stave (electrical testbed or more) within the next 6 months or so.

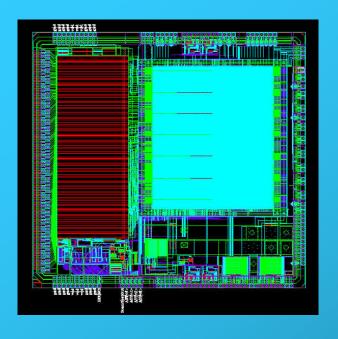
Features:

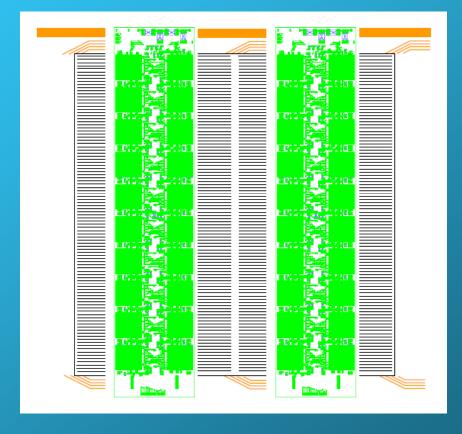
- ABC-Next 0.25 μm CMOS
- 20-chip hybrids
- p-on-p short strips sensors (sensor area 10 cm x 10 cm)
- 10 or 12 single sided modules on either side

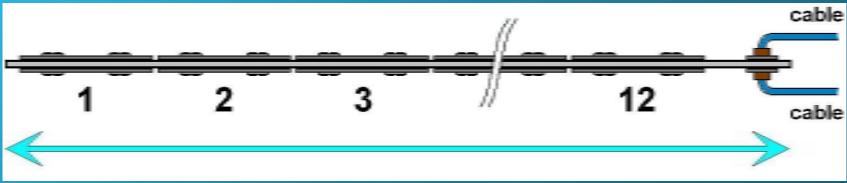
This supermodule is the best power test-bed we will get in a while. Let's make good use of it !!

First step is a power plug-in board to talk to hybrid and modules. (Next steps are not entirely clear today, but I advocate a more integrated power unit)

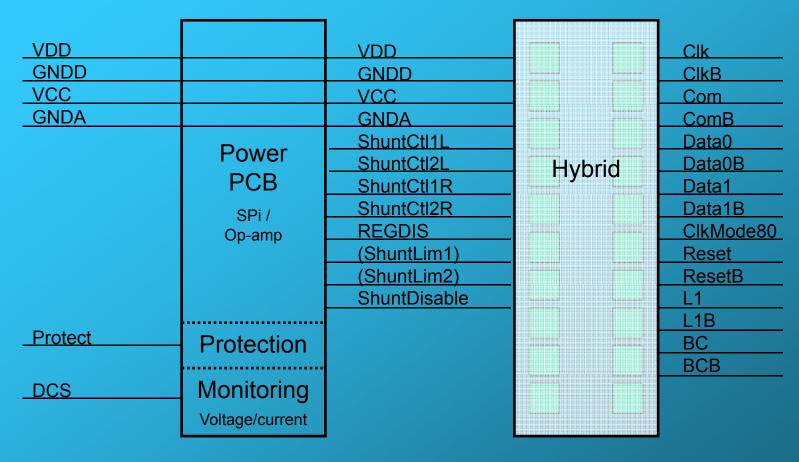
For illustration







Sketch of SP plug-in board



To stave bus cable

To hybrid

Still missing: agreed interfaces to hybrid and bus cable; definition of slow-control block; full schematic; size estimate

Plug-in boards (continued)

Each power scheme is expected to provide a plug-in board.

This is a wonderful testing opportunity for each approach and allows physicists to get used to it.

Module performance can be compared for either approach.

For now the following information is needed:

Output and input lines Size estimate Very brief description of specs (mostly gain, max. current, efficiency)

Given this, the common interfaces for all boards can be defined and we can request real-estate and a minimum number of bus lines, etc. for power ...

